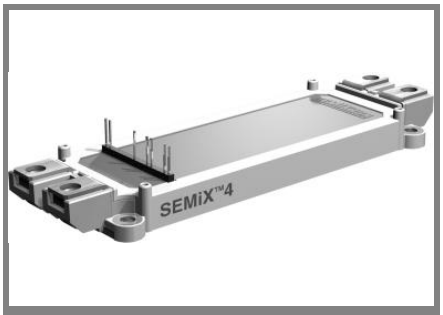
SEMiX754GB128D



SEMiX® 4

SPT IGBT Modules

SEMiX754GB128D

Target Data

Features

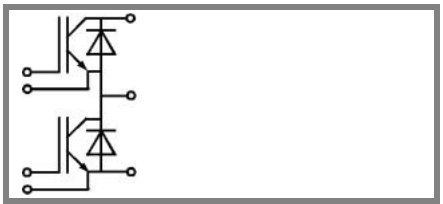
- Homogeneous Si
- SPT = Soft-Punch-Through technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability

Typical Applications

- AC inverter drives
- UPS
- Electronic welders up to 20 kHz

Absolute Maximum Ratings	T_{case} = 25°C, unless otherwise specified		
Symbol	**Conditions**	**Values**	**Units**
IGBT			
V_{CES}		1200	V
I_C	T_c = 25 (80) °C	750 (530)	A
I_{CRM}	t_p = 1 ms	800	A
V_{GES}		± 15	V
T_{vj}, (T_{stg})	$T_{OPERATION} \leq T_{stg}$	-40 ... + 150 (125)	°C
V_{isol}	AC, 1 min.	4000	V
Inverse diode			
I_F	T_c = 25 (80) °C	530 (360)	A
I_{FRM}	t_p = 1 ms	800	A
I_{FSM}	t_p = 10 ms; sin.; T_j = 25 °C	3100	A

Characteristics	T_{case} = 25°C, unless otherwise specified				
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
IGBT					
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 16 mA	4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0, V_{CE} = V_{CES}, T_j = 25 () °C		0,2	0,6	mA
$V_{CE(TO)}$	T_j = 25 (125) °C		1 (0,9)	1,15 (1,05)	V
r_{CE}	V_{GE} = 15 V, T_j = 25 (125) °C		2,3 (3)	2,9 (3,8)	mΩ
$V_{CE(sat)}$	I_{Cnom} = 400 A, V_{GE} = 15 V, T_j = 25 (125) °C, chip level	1,7	1,9 (2,1)	2,35 (2,55)	V
C_{ies}	under following conditions		36		nF
C_{oes}	V_{GE} = 0, V_{CE} = 25 V, f = 1 MHz		2,7		nF
C_{res}			1,7		nF
L_{CE}			22		nH
$R_{CC'+EE'}$	terminal-chip, T_c= 25 (125) °C		0,7 (1)		mΩ
$t_{d(on)}$/t_r	V_{CC} = 600 V, I_{Cnom} = 400 A		180 / 88		ns
$t_{d(off)}$/t_f	V_{GE} = ± 15 V		655 / 118		ns
E_{on} (E_{off})	R_{Gon} = R_{Goff} = 2,5 Ω, T_j = 125 °C		44 (48)		mJ
Inverse diode					
V_F = V_{EC}	I_{Fnom} = 400 A; V_{GE} = 0 V; T_j = 25 (125) °C, chip level		2 (1,8)	2,5 (2,3)	V
$V_{(TO)}$	T_j = 25 (125) °C		1,1	1,5 (1,3)	V
r_T	T_j = 25 (125) °C		2,3	2,5 (2,5)	mΩ
I_{RRM}	I_{Fnom} = 400 A; T_j = 25 (125) °C		367		A
Q_{rr}	di/dt = 5850 A/µs		58		µC
E_{rr}	V_{GE} = -15 V		21,5		mJ
Thermal characteristics					
$R_{th(j-c)}$	per IGBT			0,042	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,09	K/W
$R_{th(j-c)FD}$	per FWD				K/W
$R_{th(c-s)}$	per module		0,03		K/W
Temperature sensor					
R_{25}	T_c = 25 °C		5 ±5%		kΩ
$B_{25/85}$	R_2=R_1exp[B(1/T_2-1/T_1)] ; T[K];B		3420		K
Mechanical data					
M_s/M_t	to heatsink (M5) / for terminals (M6)	3/2,5		5 /5	Nm
w			390		g



GB

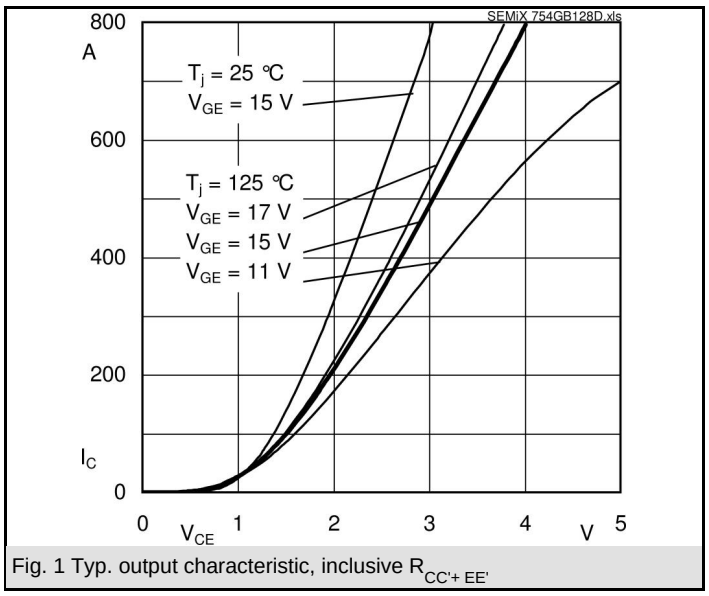


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

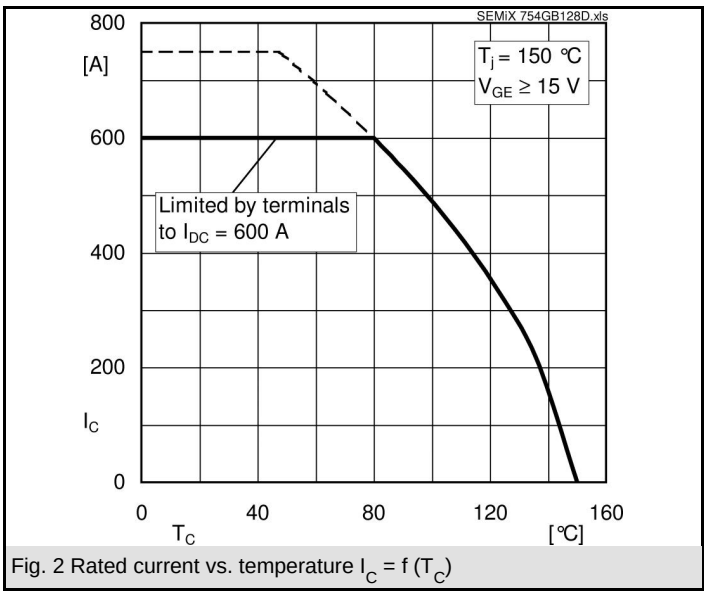


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

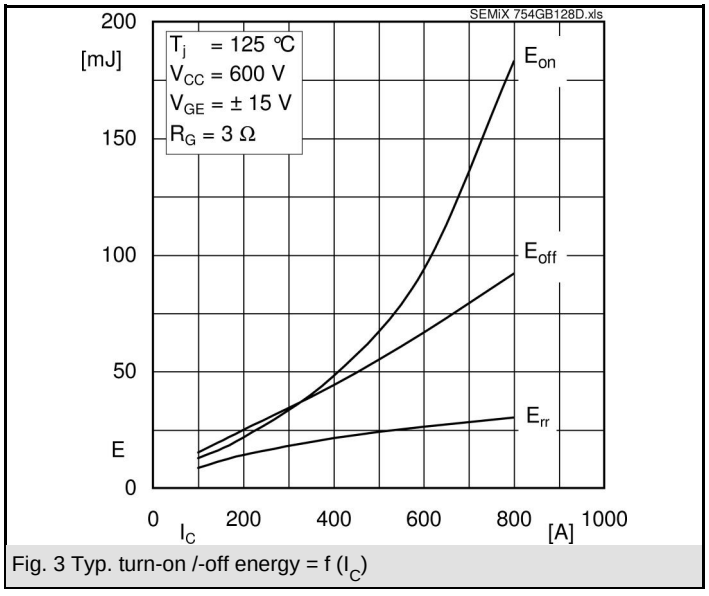


Fig. 3 Typ. turn-on /-off energy = f (I_C)

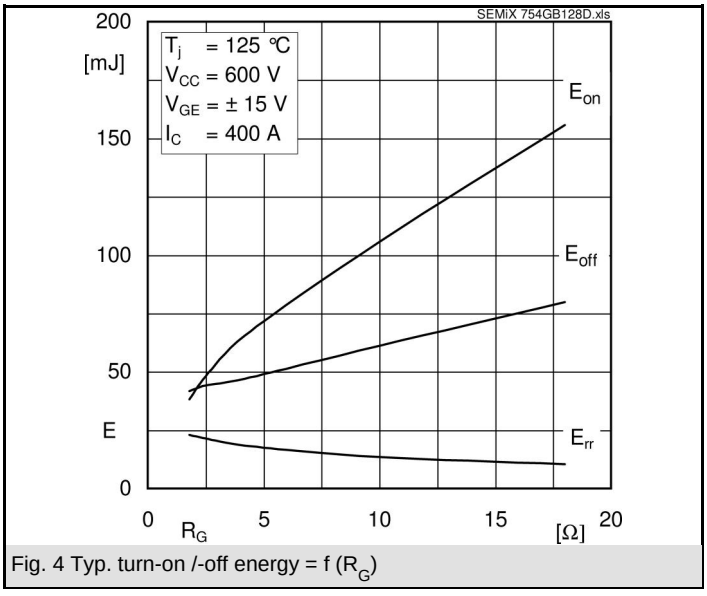


Fig. 4 Typ. turn-on /-off energy = f (R_G)

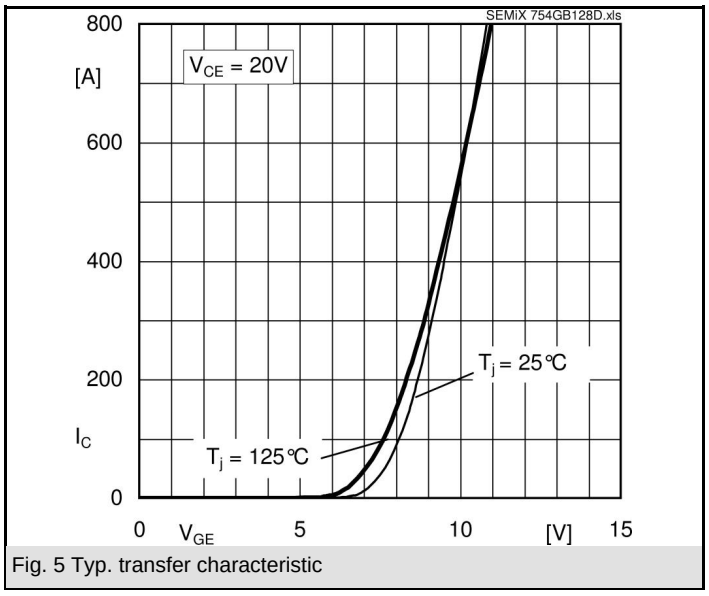


Fig. 5 Typ. transfer characteristic

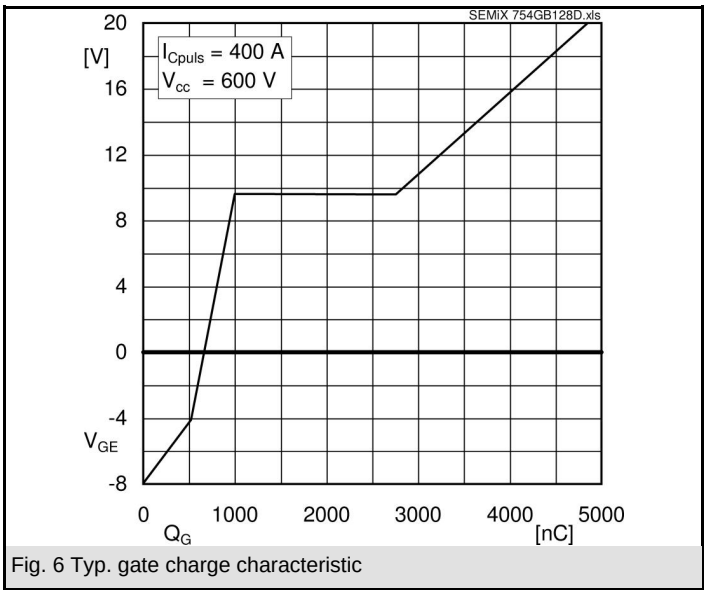


Fig. 6 Typ. gate charge characteristic

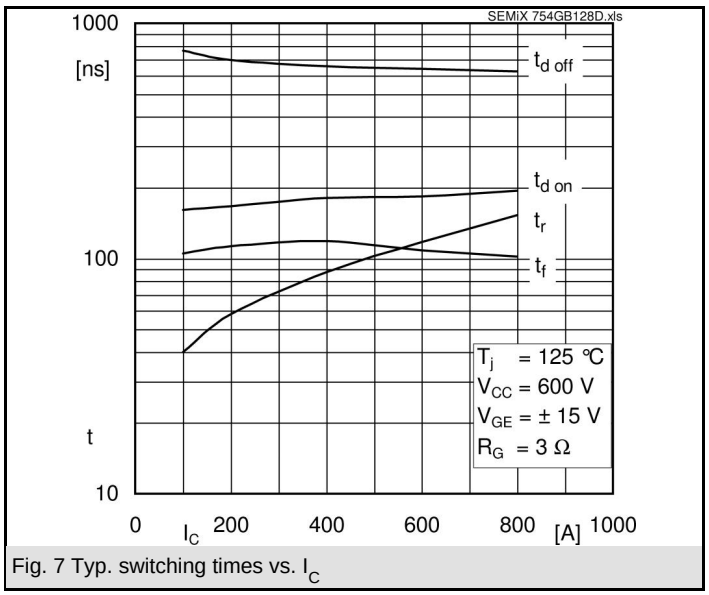


Fig. 7 Typ. switching times vs. I_C

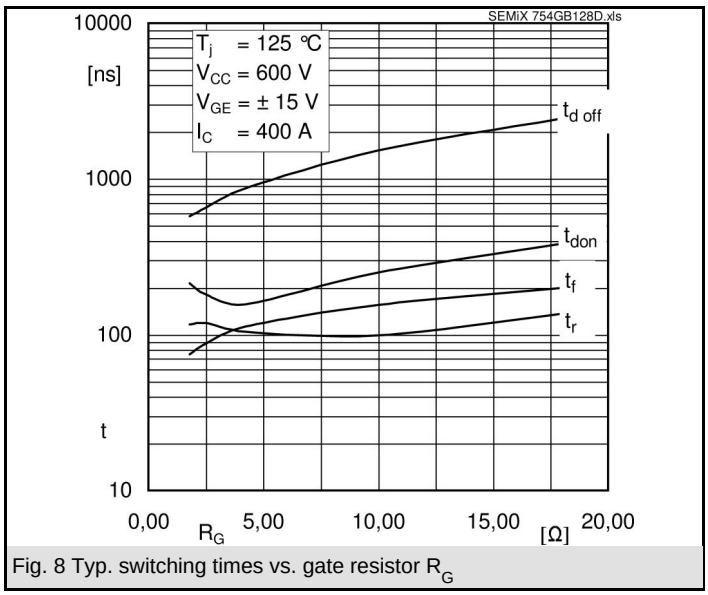


Fig. 8 Typ. switching times vs. gate resistor R_G

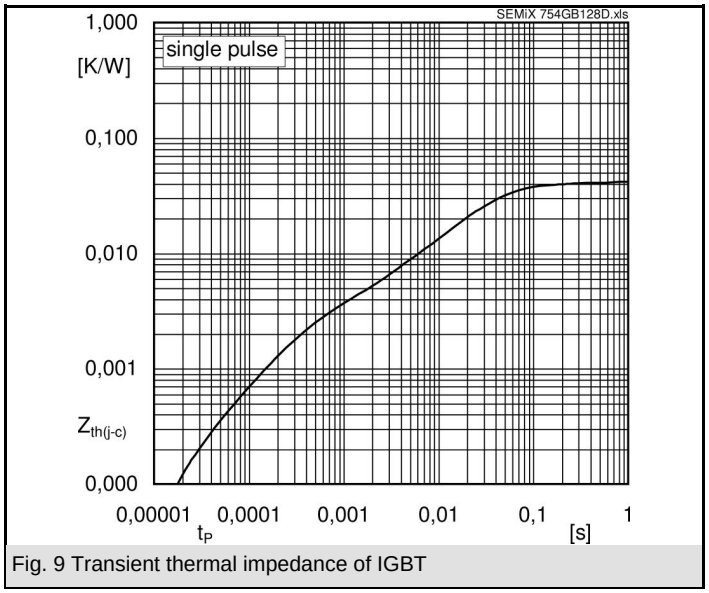


Fig. 9 Transient thermal impedance of IGBT

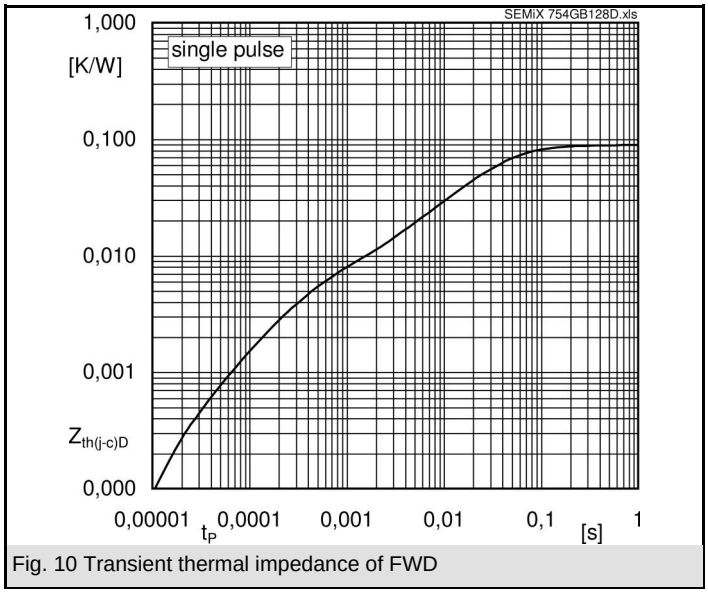


Fig. 10 Transient thermal impedance of FWD

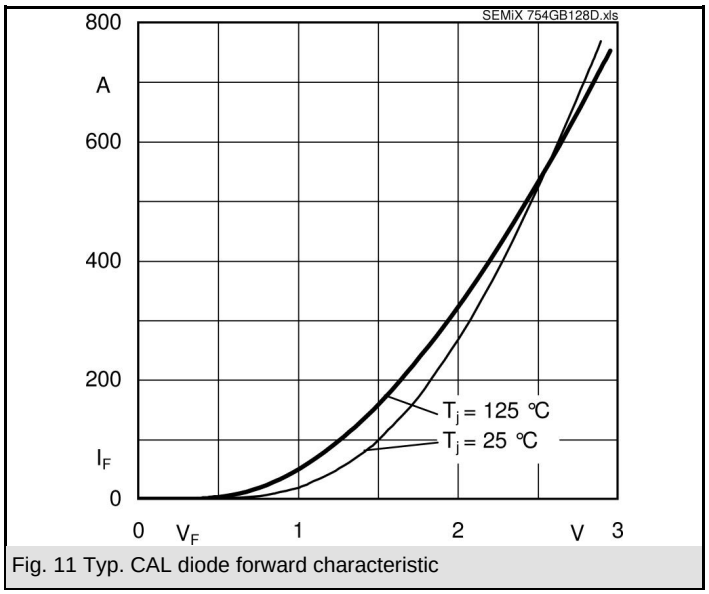


Fig. 11 Typ. CAL diode forward characteristic

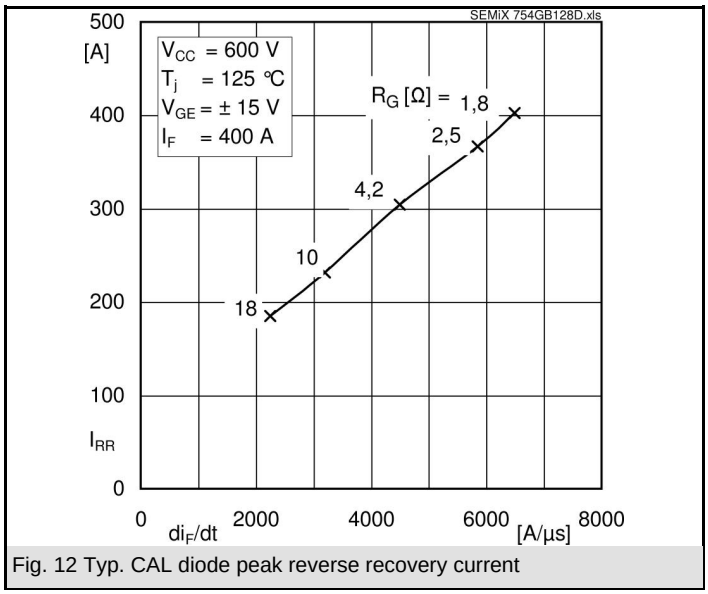


Fig. 12 Typ. CAL diode peak reverse recovery current

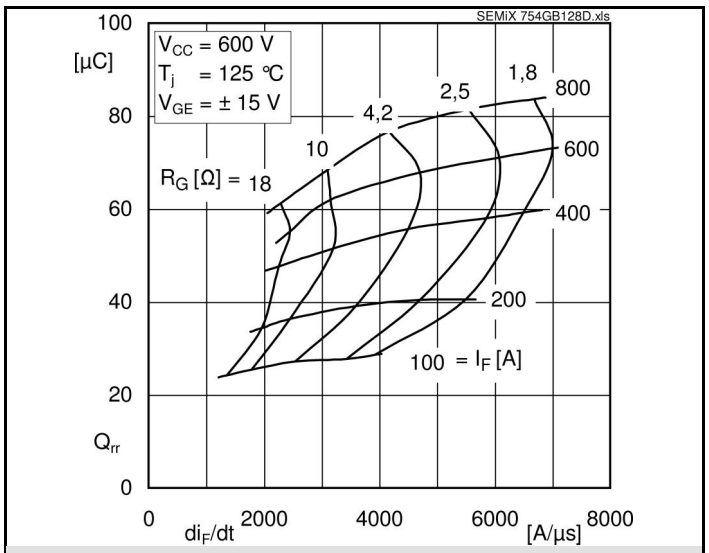
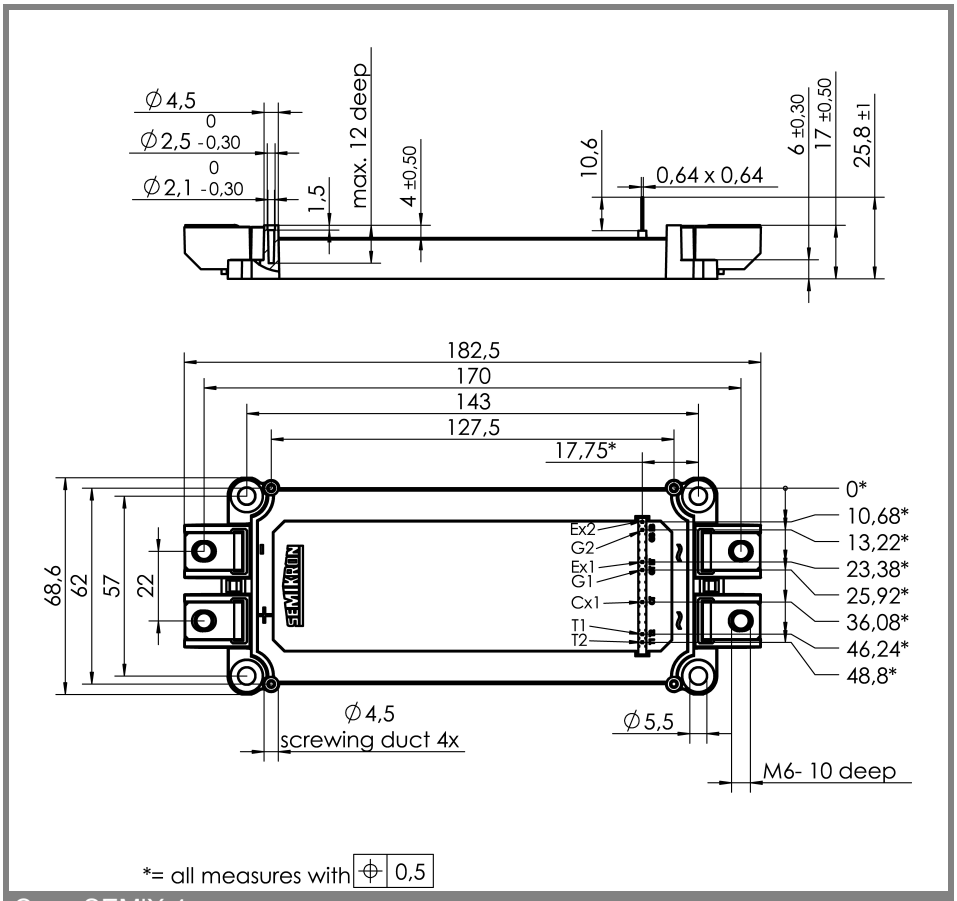
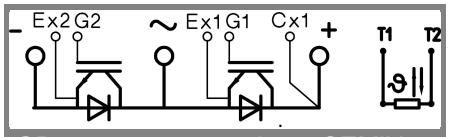


Fig. 13 Typ. CAL diode recovered charge



Case SEMiX 4



GB pinout SEMiX 4

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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